

April 2009

ISL9R460PF2

4A, 600V Stealth™ Diode

General Description

The ISL9R460PF2 is a StealthTM diode optimized for low loss performance in high frequency hard switched applications. The StealthTM family exhibits low reverse recovery current (I_{RRM}) and exceptionally soft recovery under typical operating conditions.

This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low I_{RBM} and short t_a phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the Stealth™ diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

Formerly developmental type TA49408.

CATHODE

Features

•	Soft Recovery $t_b / t_a > 3$
•	Fast Recovery t_{rr} < 20ns
•	Operating Temperature
•	Reverse Voltage 600V

Avalanche Energy Rated

Applications

- Switch Mode Power Supplies
- · Hard Switched PFC Boost Diode
- UPS Free Wheeling Diode
- Motor Drive FWD
- SMPS FWD
- · Snubber Diode

Package Symbol



TO-220F





Device Maximum Ratings T_C= 25°C unless otherwise noted

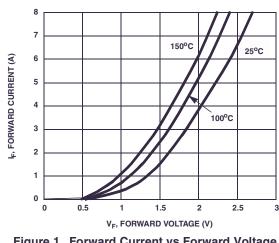
Symbol	Parameter	Ratings	Units
V _{RRM}	Peak Repetitive Reverse Voltage	600	V
V _{RWM}	Working Peak Reverse Voltage	600	V
V _R	DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current (T _C = 108°C)	4	Α
I _{FRM}	Repetitive Peak Surge Current (20kHz Square Wave)	8	Α
I _{FSM}	Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60Hz)	50	Α
P _D	Power Dissipation	22	W
E _{AVL}	Avalanche Energy (0.5A, 80mH)	10	mJ
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to 150	°C
TL	Maximum Temperature for Soldering		
T_{PKG}^{-}	Leads at 0.063in (1.6mm) from Case for 10s	300	°C
	Package Body for 10s, See Techbrief TB334	260	°C

CAUTION: Stresses above those listed in "Device Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Device Marking	Device	Package	Tape Width	Quantity
R460PF2	ISL9R460PF2	TO-220F	N/A	50 Units

Symbol	Parameter	Test (Conditions	Min	Тур	Max	Units
Off State Characteristics							
I _R	Instantaneous Reverse Current	V _R = 600V	T _C = 25°C	-	-	100	μΑ
			T _C = 125°C	-	-	1.0	mA
On State	Characteristics						
V _F	Instantaneous Forward Voltage	I _F = 4A	T _C = 25°C	-	2.0	2.4	V
·			T _C = 125°C	-	1.6	2.0	V
Dynamic	Characteristics						
C_{J}	Junction Capacitance	$V_{R} = 10V, I_{F} = 0$	Α	-	19	-	pF
t _{rr}	Reverse Recovery Time	$I_F = 1A$, $dI_F/dt = 100A/\mu s$, $V_R = 30V$		-	17	20	ns
۲rr	neverse necovery fillie	$I_F = 1A$, $dI_F/dt = 100A/\mu s$, $V_R = 30V$ $I_F = 4A$, $dI_F/dt = 100A/\mu s$, $V_R = 30V$		-	19	22	
							l ns
†	Reverse Recovery Time	_	100A/μs, V _R = 30V	-		-	ns
t _{rr}	Reverse Recovery Time Maximum Reverse Recovery Current	$I_F = 4A$, $dI_F/dt = I_F = 4A$, $dI_F/dt = 200A/\mu s$			17 2.6		ns ns A
I _{RRM}	Reverse Recovery Time Maximum Reverse Recovery Current Reverse Recovered Charge	$I_F = 4A$,	5,	-	17	-	ns
I _{RRM} Q _{RR}	Maximum Reverse Recovery Current	$I_F = 4A,$ $dI_F/dt = 200A/\mu$	5,	-	17 2.6	-	ns A
I _{RRM}	Maximum Reverse Recovery Current Reverse Recovered Charge		s, = 25°C	-	17 2.6 22	-	ns A nC
I _{RRM} Q _{RR} t _{rr}	Maximum Reverse Recovery Current Reverse Recovered Charge Reverse Recovery Time	$I_F = 4A,$ $dI_F/dt = 200A/\mu$ $V_R = 390V, T_C = I_F = 4A,$ $dI_F/dt = 200A/\mu$ $V_R = 390V,$	s, = 25°C	- - -	17 2.6 22 77	-	ns A nC
I _{RRM} Q _{RR} t _{rr} S	Maximum Reverse Recovery Current Reverse Recovered Charge Reverse Recovery Time Softness Factor (t _b /t _a)		s, = 25°C		17 2.6 22 77 4.2		ns A nC ns
I _{RRM} Q _{RR} t _{rr} S I _{RRM}	Maximum Reverse Recovery Current Reverse Recovered Charge Reverse Recovery Time Softness Factor (t _b /t _a) Maximum Reverse Recovery Current	$I_F = 4A,$ $dI_F/dt = 200A/\mu$ $V_R = 390V, T_C = I_F = 4A,$ $dI_F/dt = 200A/\mu$ $V_R = 390V,$	s, = 25°C		17 2.6 22 77 4.2 2.8		ns A nC ns
I _{RRM} Q _{RR} t _{rr} S I _{RRM} Q _{RR}	Maximum Reverse Recovery Current Reverse Recovered Charge Reverse Recovery Time Softness Factor (t _b /t _a) Maximum Reverse Recovery Current Reverse Recovered Charge	$\begin{aligned} & I_F = 4A, \\ & dI_F/dt = 200A/\mu; \\ & V_R = 390V, \ T_C = \\ & I_F = 4A, \\ & dI_F/dt = 200A/\mu; \\ & V_R = 390V, \\ & T_C = 125^{\circ}C \\ & I_F = 4A, \\ & dI_F/dt = 400A/\mu; \end{aligned}$	s, = 25°C s,	- - - - -	17 2.6 22 77 4.2 2.8 100	- - - -	ns A nC ns A nC
IRRM QRR trr S IRRM QRR trr rr	Maximum Reverse Recovery Current Reverse Recovered Charge Reverse Recovery Time Softness Factor (t _b /t _a) Maximum Reverse Recovery Current Reverse Recovered Charge Reverse Recovery Time	$\begin{aligned} & I_F = 4A, \\ & dI_F/dt = 200A/\mu \\ & V_R = 390V, \ T_C = \\ & I_F = 4A, \\ & dI_F/dt = 200A/\mu \\ & V_R = 390V, \\ & T_C = 125^{\circ}C \\ & I_F = 4A, \\ & dI_F/dt = 400A/\mu \\ & V_R = 390V, \end{aligned}$	s, = 25°C s,	- - - - - -	17 2.6 22 77 4.2 2.8 100 54	- - - - - -	ns A nC ns A nC
IRRM QRR trr S IRRM QRR trr S	Maximum Reverse Recovery Current Reverse Recovered Charge Reverse Recovery Time Softness Factor (t _b /t _a) Maximum Reverse Recovery Current Reverse Recovered Charge Reverse Recovery Time Softness Factor (t _b /t _a)	$\begin{aligned} & I_F = 4A, \\ & dI_F/dt = 200A/\mu; \\ & V_R = 390V, \ T_C = \\ & I_F = 4A, \\ & dI_F/dt = 200A/\mu; \\ & V_R = 390V, \\ & T_C = 125^{\circ}C \\ & I_F = 4A, \\ & dI_F/dt = 400A/\mu; \end{aligned}$	s, = 25°C s,		17 2.6 22 77 4.2 2.8 100 54 3.5		ns A nC ns A nC ns

$R_{\theta JC}$	Thermal Resistance Junction to Case		-	-	5.7	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	TO-220F	-	-	70	°C/W



Typical Performance Curves $T_C = 25^{\circ}C$ unless otherwise noted

Figure 1. Forward Current vs Forward Voltage

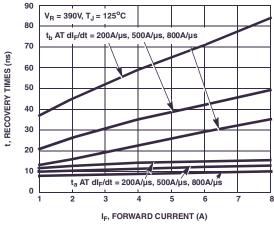


Figure 3. t_a and t_b Curves vs Forward Current

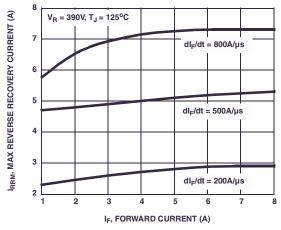


Figure 5. Maximum Reverse Recovery Current vs **Forward Current**

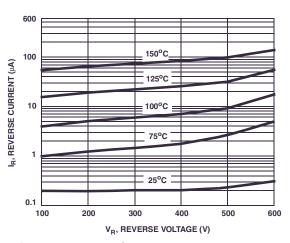


Figure 2. Reverse Current vs Reverse Voltage

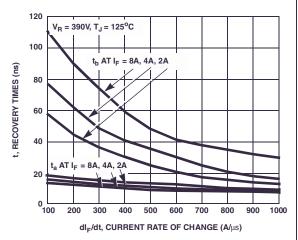


Figure 4. t_a and t_b Curves vs dl_F/dt

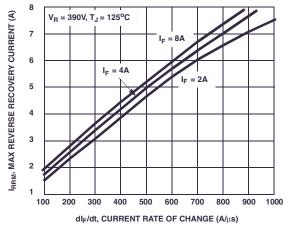
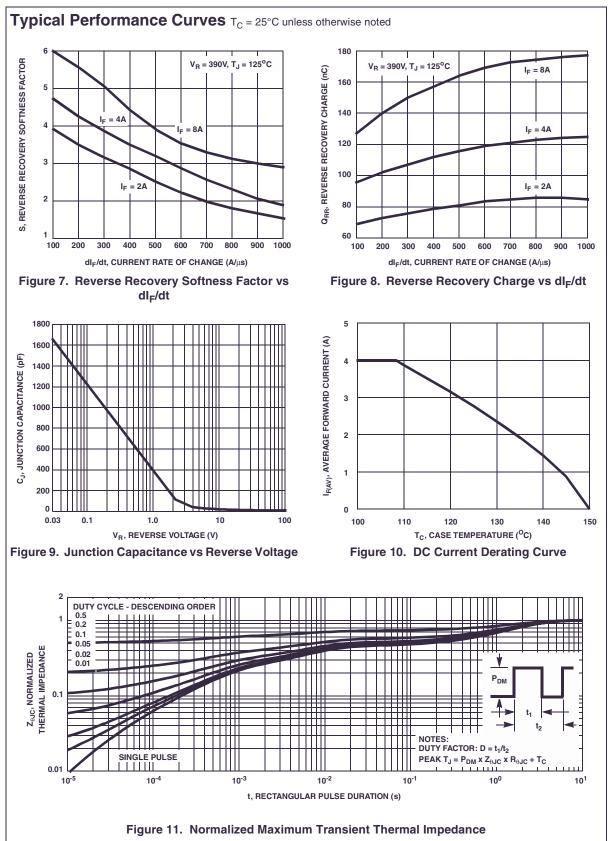
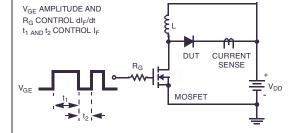


Figure 6. Maximum Reverse Recovery Current vs dl_E/dt



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Test Circuit and Waveforms



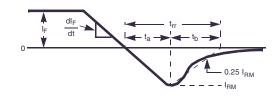


Figure 12. It_{rr} Test Circuit

Figure 13. t_{rr} Waveforms and Definitions

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I = 0.5A
L = 80mH
R < 0.1\Omega
V_{DD} = 200V
E_{AVL} = 1/2LI^2 \left[ V_{R(AVL)} / (V_{R(AVL)} - V_{DD}) \right]
Q_1 = IGBT \left( BV_{CES} > DUT \ V_{R(AVL)} \right)
L
CURRENT
SENSE
V_{DD}
V_{DD}
DUT
```

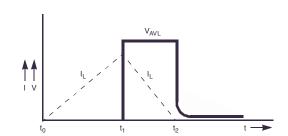
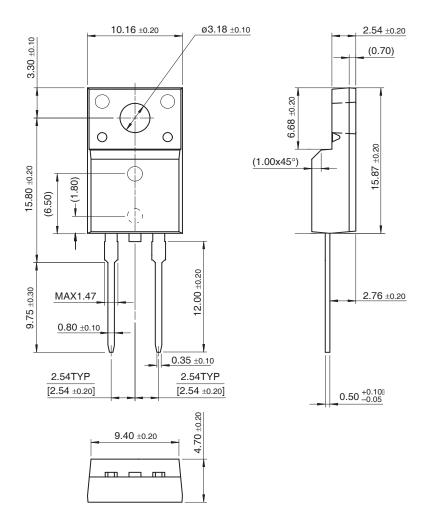


Figure 14. Avalanche Energy Test Circuit

Figure 15. Avalanche Current and Voltage Waveforms

Mechanical Dimensions

TO-220F 2L



Dimensions in Millimeters





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